

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

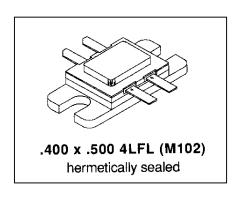
PHONE: (215) 631-9840 FAX: (215) 631-9855

MS2200

RF AND MICROWAVE TRANSISTORS UHF PULSED APPLICATIONS

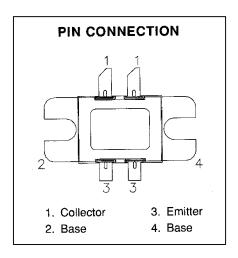
Features

- 500 Watts @ 250 μSec Pulse Width, 10% Duty Cycle
- Refractory Gold Metallization
- Emitter Ballasting And Low Resistance For Reliability and Ruggedness
- Infinite VSWR Capability At Specified Operating Conditions
- Input Matched, Common Base Configuration
- Balanced Configuration



DESCRIPTION:

The MS2200 is a hermetically sealed, gold metallized silicon NPN pulse power transistor mounted in a common base balanced configuration. The MS2200 is designed for applications requiring high peak power and low duty cycles within the frequency range of 400 – 500 MHz.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	65	V
V _{CES}	Collector-Emitter Voltage	65	V
V _{EBO}	Emitter-Base Voltage	3.5	V
Ic	Device Current	43.2	Α
P _{DISS}	Power Dissipation	1167	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	0.15	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions	Value			Units
Syllibol	rest conditions	Min.	Тур.	Max.	Ullits
BV _{CBO}	$I_C = 50 \text{ mA}$ $I_E = 0 \text{ mA}$	65			V
BV _{CES}	$I_C = 50 \text{ mA}$ $V_{BE} = 0 \text{ V}$	65			٧
BV _{EBO}	$I_E = 10 \text{ mA}$ $I_C = 0 \text{ mA}$	3.5			٧
$I_{\sf CES}$	$V_{CE} = 30 \text{ V}$ $I_E = 0 \text{ mA}$			15	mA
h _{FE}	$V_{CE} = 5 V$ $I_C = 5 A$	20		200	

DYNAMIC

Symbol	Test Conditions		Value		Units
Syllibol	rest conditions	Min.	Тур.	Max.	Ullits
P _{out}	$f = 425 \text{ MHz}$ $P_{IN} = 54 \text{ W}$ $V_{CE} = 40 \text{ V}$	500			W
G₽	$f = 425 \text{ MHz}$ $P_{IN} = 54 \text{ W}$ $V_{CE} = 40 \text{ V}$	9.7			Db
ης	$f = 425 \text{ MHz}$ $P_{IN} = 54 \text{ W}$ $V_{CE} = 40 \text{ V}$	50			%

Note:

Pulse Width = $250\mu Sec$, Duty Cycle = 10%

This device is suitable for use under other pulse width/duty cycle conditions.

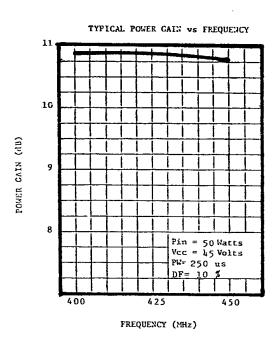
Please contact the factory for specific applications assistance.



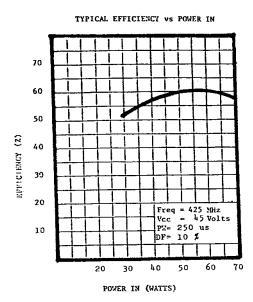
TYPICAL PERFORMANCE POWER OUTPUT vs POWER INPUT

TYPICAL POWER OUT VS POWER IN 700 600 (WATTS) 500 POWER OUT 400 Freq = 425 MHz Vcc = 40, 45V PW=250us 300 10 20 30 40 50 60 70 POWER IN (WATTS)

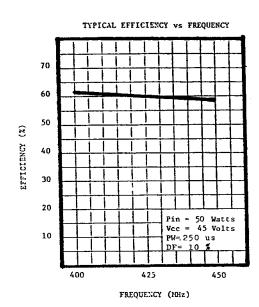
POWER GAIN vs FREQUENCY



EFFICIENCY vs POWER INPUT



EFFICIENCY vs FREQUENCY



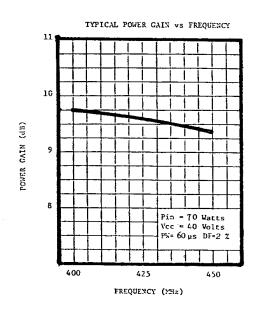


TYPICAL PERFORMANCE (CONTINUED)

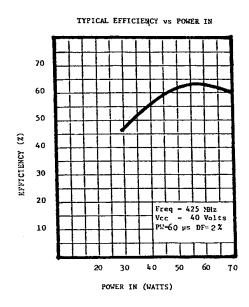
POWER OUTPUT vs POWER INPUT

TYPICAL POWER OUT VS POWER IN 600 500 Freq = 425 MHz Vcc = 40, 45V PW= 60usDF= 2% 10 20 30 40 50 60 70 POWER IN (WATTS)

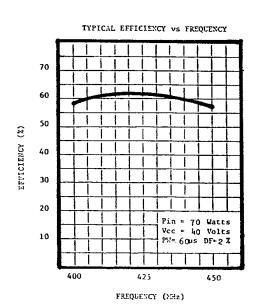
POWER GAIN vs FREQUENCY



EFFICIENCY vs POWER INPUT

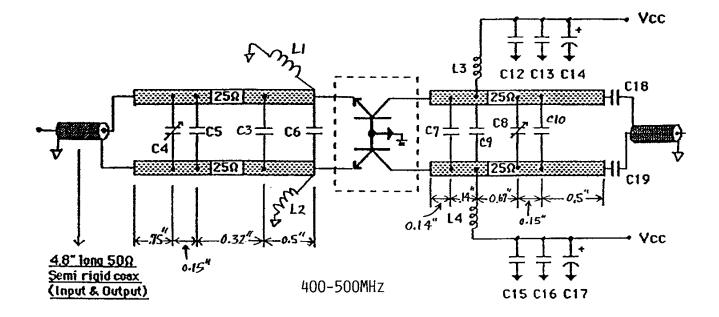


EFFICIENCY vs FREQUENCY





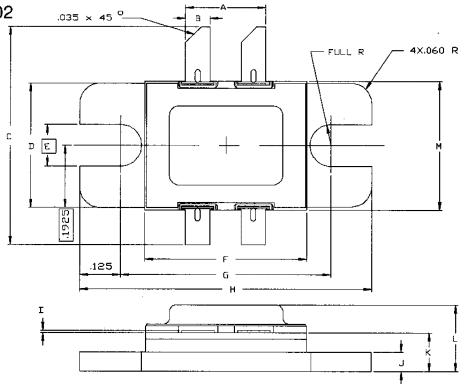
TEST CIRCUIT





PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0102



ADVANCED POWER TECHNOLOGY			CONT/D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
Α	.240/6,10	.254/6,45	к	.115/2,92	.130/3,30
В	,070/1,78	.080/2,03	L		.230/5,84
C	.780/19,81	.820/20,83	М	.395/10,03	.407/10,34
D	.380/9,65	.390/9,91			
E	.130/3,30				
F	.495/12,57	.507/12,88			
G	.640/16,26	.655/16,64			
Н	.890/22,61	.910/23,11			
I	.002/0,05	.006/0,15			
ل	.058/1,47	.065/1,65			

AMEYA360 Components Supply Platform

Authorized Distribution Brand:

























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